Yoichi Yamada

List of Publications by Year
in descending order

135 papers	2,165 citations	236925 25 h-index	276875 41 g-index
135 all docs	135 docs citations	135 times ranked	1484 citing authors

#	Article	IF	Citations
1	Highly Transparent pâ€AlGaNâ€Based (326â€“341 nm)â€Band Ultravioletâ€A Lightâ€Emitting Diodes on AlN Templates: Recent Advances and Perspectives. Physica Status Solidi (A) Applications and Materials Science, 2022, 219, .	1.8	2
2	Achieving 9.6% efficiency in 304Ânm p-AlGaN UVB LED via increasing the holes injection and light reflectance. Scientific Reports, 2022, 12, 2591.	3.3	38
3	Study on higher-energy emission observed locally around V-pits on InGaN/GaN quantum wells grown on moderate-temperature GaN. Journal of Applied Physics, 2021, 130, 053103.	2.5	0
4	Evaluation of internal quantum efficiency and stimulated emission characteristics in AlGaN-based multiple quantum wells. Japanese Journal of Applied Physics, 2021, 60, 120503.	1.5	6
5	Extremely high internal quantum efficiency of AlGaN-based quantum wells on face-to-face annealed sputter-deposited AlN templates. Applied Physics Express, 2021, 14, 122004.	2.4	6
6	High internal quantum efficiency and optically pumped stimulated emission in AlGaN-based UV-C multiple quantum wells. Applied Physics Letters, 2020, 117, .	3.3	28
7	Correlation between excitons recombination dynamics and internal quantum efficiency of AlGaN-based UV-A multiple quantum wells. Journal of Applied Physics, 2020, 128, .	2.5	23
8	External Quantum Efficiency of 6.5% at 300 nm Emission and 4.7% at 310 nm Emission on Bare Wafer of AlGaN-Based UVB LEDs. ACS Applied Electronic Materials, 2020, 2, 1892-1907.	4.3	45
9	Beyond 53% internal quantum efficiency in a AlGaN quantum well at 326â€‰â€‰nm UVA emission and single-peak operation of UVA LED. Optics Letters, 2020, 45, 495.	3.3	26
10	Beyond 53% internal quantum efficiency in a AlGaN quantum well at 326â€‰â€‰nm UVA emission and single-peak operation of UVA LED: publisherâ€™s note. Optics Letters, 2020, 45, 2563.	3.3	7
11	13 mW operation of a 295â€“310 nm AlGaN UV-B LED with a p-AlGaN transparent contact layer for real world applications. Journal of Materials Chemistry C, 2019, 7, 143-152.	5.5	84
12	Temperature-dependent cathodoluminescence mapping of InGaN epitaxial layers with different In compositions. Japanese Journal of Applied Physics, 2019, 58, SCCB13.	1.5	0
13	Analysis of efficiency curves in near-UV, blue, and green-emitting InGaN-based multiple quantum wells using rate equations of exciton recombination. Japanese Journal of Applied Physics, 2019, 58, SCCB02.	1.5	11
14	Effects of saturation of nonradiative recombination centers on internal quantum efficiency in InGaN light-emitting diodes. Japanese Journal of Applied Physics, 2019, 58, 011003.	1.5	7
15	Recent Progress Toward Realizing AlGaN-Based Deep-UV Laser Diodes. The Review of Laser Engineering, 2019, 47, 196.	0.0	3
16	Temperature Dependence of Stokes Shifts of Excitons and Biexcitons in Al_{0.61}Ga_{0.39}N Epitaxial Layer. Physica Status Solidi (B): Basic Research, 2018, 255, 1700374.	1.5	4
17	Separation of effects of InGaN/GaN superlattice on performance of light-emitting diodes using mid-temperature-grown GaN layer. Japanese Journal of Applied Physics, 2018, 57, 062101.	1.5	13
18	Spatially Resolved Spectroscopy of Blue and Green InGaN Quantum Wells by Scanning Nearâ€Field Optical Microscopy. Physica Status Solidi (B): Basic Research, 2018, 255, 1700322.	1.5	3

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19	Potential Barrier Formed Around Dislocations in InGaN Quantum Well Structures by Spot Cathodoluminescence Measurements. Physica Status Solidi (B): Basic Research, 2018, 255, 1700358.	1.5	13
20	Nanoscopic spectroscopy of potential barriers formed around V-pits in InGaN/GaN multiple quantum wells on moderate temperature GaN pit expansion layers. Journal of Applied Physics, 2018, 124, .	2.5	7
21	Cathodoluminescence study on local high-energy emissions at dark spots in AlGaN/AlGaN multiple quantum wells. Japanese Journal of Applied Physics, 2018, 57, 060311.	1.5	2
22	Temperature dependence of excitonic transitions in Al0.60Ga0.40N/Al0.70Ga0.30N multiple quantum wells from 4 to 750â€‰K. Journal of Applied Physics, 2018, 123, .	2.5	4
23	High-temperature photoluminescence and photoluminescence excitation spectroscopy of Al_{0.60}Ga_{0.40}N/Al_{0.70}Ga_{0.30}N multiple quantum wells. Applied Physics Express, 2017, 10, 021002.	2.4	8
24	Confinement-enhanced biexciton binding energy in AlGaN-based quantum wells. Applied Physics Express, 2017, 10, 051003.	2.4	2
25	Microscopic potential fluctuations in Si-doped AlGaN epitaxial layers with various AlN molar fractions and Si concentrations. Journal of Applied Physics, 2016, 119, .	2.5	5
26	Cerium oxide and hydrogen co-doped indium oxide films for high-efficiency silicon heterojunction solar cells. Solar Energy Materials and Solar Cells, 2016, 149, 75-80.	6.2	92
27	Excitation density dependence of radiative and nonradiative recombination lifetimes in InGaN/GaN multiple quantum wells. Physica Status Solidi (B): Basic Research, 2015, 252, 940-945.	1.5	16
28	Controlling potential barrier height by changing V-shaped pit size and the effect on optical and electrical properties for InGaN/GaN based light-emitting diodes. Journal of Applied Physics, 2015, 117, .	2.5	40
29	Inhomogeneous distribution of defect-related emission in Si-doped AlGaN epitaxial layers with different Al content and Si concentration. Journal of Applied Physics, 2014, 115, .	2.5	21
30	Binding energy of localized biexcitons in AlGaN-based quantum wells. Applied Physics Express, 2014, 7, 122101.	2.4	8
31	Si concentration dependence of structural inhomogeneities in Si-doped AlxGa1â^'xN/AlyGa1â^'yN multiple quantum well structures (xâ€‰=â€‰0.6) and its relationship with internal quantum efficiency. Journal of Applied Physics, 2014, 116, .	2.5	5
32	Recombination dynamics and internal quantum efficiency in InGaN. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 652-655.	0.8	2
33	Time and Spatially Resolved Luminescence Spectroscopy of ZnO Nanostructures. Springer Series in Materials Science, 2014, , 195-216.	0.6	0
34	Effects of exciton localization on internal quantum efficiency of InGaN nanowires. Journal of Applied Physics, 2013, 114, .	2.5	38
35	Cathodoluminescence Study of Optical Inhomogeneity in Si-Doped AlGaN Epitaxial Layers Grown by Low-Pressure Metalorganic Vapor-Phase Epitaxy. Japanese Journal of Applied Physics, 2013, 52, 08JL07.	1.5	6
36	Emission Wavelength Dependence of Internal Quantum Efficiency in InGaN Nanowires. Japanese Journal of Applied Physics, 2013, 52, 08JE10.	1.5	9

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37	Fabrication and Evaluation of GaN Layer Composed ofm- and {1011} Facet Structure. Japanese Journal of Applied Physics, 2013, 52, 01AF06.	1.5	0
38	Photoluminescence due to Inelastic Biexciton Scattering from an Al$_{0.61}$Ga$_{0.39}$N Ternary Alloy Epitaxial Layer at Room Temperature. Applied Physics Express, 2012, 5, 072401.	2.4	8
39	Dependence of internal quantum efficiency on doping region and Si concentration in Al-rich AlGaN quantum wells. Applied Physics Letters, 2012, 101, 042110.	3.3	45
40	Spatial Inhomogeneity of Aluminum Content in Air-Bridged Lateral Epitaxially Grown AlGaN Ternary Alloy Films Probed by Cross-Sectional Scanning Near-Field Optical Microscopy. Japanese Journal of Applied Physics, 2012, 51, 035604.	1.5	1
41	Internal Quantum Efficiency and Nonradiative Recombination Rate in InGaN-Based Near-Ultraviolet Light-Emitting Diodes. Japanese Journal of Applied Physics, 2012, 51, 072102.	1.5	43
42	Correlation between in-plane strain and optical polarization of Si-doped AlGaN epitaxial layers as a function of Al content and Si concentration. Journal of Applied Physics, 2012, 112, 033512.	2.5	8
43	Structural and optical evaluation of InGaN/GaN multi-quantum wells on template consisting of in-plane alternately arranged relaxed InGaN and GaN. Journal of Applied Physics, 2012, 111, 043508.	2.5	6
44	AlN homoepitaxial growth on sublimation-AlN substrate by low-pressure HVPE. Journal of Crystal Growth, 2012, 350, 69-71.	1.5	24
45	Internal Quantum Efficiency and Nonradiative Recombination Rate in InGaN-Based Near-Ultraviolet Light-Emitting Diodes. Japanese Journal of Applied Physics, 2012, 51, 072102.	1.5	62
46	Spatial Inhomogeneity of Aluminum Content in Air-Bridged Lateral Epitaxially Grown AlGaN Ternary Alloy Films Probed by Cross-Sectional Scanning Near-Field Optical Microscopy. Japanese Journal of Applied Physics, 2012, 51, 035604.	1.5	0
47	Bowing of biexciton binding in Al x Ga 1-x N ternary alloys. Proceedings of SPIE, 2011, , .	0.8	0
48	Recombination dynamics of localized excitons in AlxGa1-xN (0.37<x<0.81) ternary alloys. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2133-2135.	0.8	6
49	Ultraviolet biexcitonic emission from AlGaN ternary alloys. Electronics and Communications in Japan, 2011, 94, 41-47.	0.5	0
50	Huge binding energy of localized biexcitons in Al-rich AlxGa1â^'xN ternary alloys. Applied Physics Letters, 2011, 98, 081907.	3.3	8
51	Silicon concentration dependence of optical polarization in AlGaN epitaxial layers. Applied Physics Letters, 2011, 98, .	3.3	14
52	Localization dynamics of biexcitons and electronâ€“hole plasmas in GaNâ€based mixed crystals. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 33-36.	1.8	0
53	Exciton localization in Alâ€rich AlGaN ternary alloy epitaxial layers. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 1884-1886.	0.8	3
54	Ultrafast decay of photoluminescence from high-density excitons inAlxGa1â^'xNmixed crystals: Diffusive propagation of exciton-polaritons. Physical Review B, 2010, 82, .	3.2	5

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55	Recombination dynamics of excitons in phosphorus-doped ZnO nanostructures. , 2010, , .		0
56	Composition dependent dynamics of biexciton localization in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>Al</mml:mtext></mml:mrow><mml:mi>x</mml:mi></mml:msub> crystals. Physical Review B, 2009, 80, .	3.2	3
57	Spatially separated intrinsic emission components in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>In</mml:mtext></mml:mrow><mml:mi>x</mml:mi></mml:msub> alloys. Physical Review B, 2009, 80, .	3.2	16
58	Discrete luminescence bands in AlGaN-based quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S767-S771.	0.8	0
59	Temperature dependence of excitonic transitions in a-plane AlN epitaxial layers. Journal of Applied Physics, 2009, 105, 083533.	2.5	17
60	Recombination dynamics of localized excitons in AlGaN-based quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2274-2276.	0.8	1
61	Temperature dependence of localized exciton transitions in AlGaN ternary alloy epitaxial layers. Journal of Applied Physics, 2008, 104, .	2.5	33
62	Dynamics of biexciton localization in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>Al</mml:mtext></mml:mrow><mml:mi>x</mml:mi></mml:msub> crystals under exciton resonant excitation. Physical Review B, 2008, 77, .	3.2	5
63	Photoluminescence from highly excited AlN epitaxial layers. Applied Physics Letters, 2008, 92, .	3.3	31
64	Internal Quantum Efficiency of Nitride-based Light-Emitting Diodes. Journal of Light and Visual Environment, 2008, 32, 191-195.	0.2	14
65	Ultraviolet Biexcitonic Emission from AlGaN Ternary Alloys. IEEJ Transactions on Electronics, Information and Systems, 2008, 128, 757-762.	0.2	0
66	Population dynamics of localized biexcitons in AlxGa1â^'xN ternary alloys. Applied Physics Letters, 2007, 91, .	3.3	3
67	Localization-induced inhomogeneous screening of internal electric fields in AlGaN-based quantum wells. Applied Physics Letters, 2007, 91, .	3.3	14
68	Fundamental Properties of Wide Bandgap Semiconductors. , 2007, , 25-96.		0
69	Optical Properties of ZnCdS:I Orange and ZnSTe:I White Thin Film Phosphor for High Ra White LED. Journal of Light and Visual Environment, 2007, 31, 61-64.	0.2	1
70	Recombination dynamics of localized biexcitons in AlGaN ternary alloys (Invited Paper). , 2005, , .		2
71	Biexciton luminescence from AlxGa1â^'xN epitaxial layers. Applied Physics Letters, 2004, 84, 2082-2084.	3.3	18
72	Spatially resolved cathodoluminescence study on AlGaN layer fabricated by air-bridged lateral epitaxial growth. Physica Status Solidi (B): Basic Research, 2004, 241, 2730-2734.	1.5	5

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73	Time-resolved nonlinear luminescence of excitonic transitions in GaN. Journal of Applied Physics, 2004, 96, 138-143.	2.5	3
74	Stokes shift of biexcitons inAlxGa1â^'xNepitaxial layers. Physical Review B, 2004, 70, .	3.2	23
75	Temperature dependence of Stokes shift in InxGa1â^'xN epitaxial layers. Journal of Applied Physics, 2003, 93, 1642-1646.	2.5	30
76	Temperature dependence of free-exciton luminescence in cubic CdS films. Applied Physics Letters, 2003, 82, 388-390.	3.3	30
77	Internal quantum efficiency of highly-efficient InxGa1â^'xN-based near-ultraviolet light-emitting diodes. Applied Physics Letters, 2003, 83, 4906-4908.	3.3	275
78	Intense Ultraviolet Electroluminescence Properties of the High-Power InGaN-Based Light-Emitting Diodes Fabricated on Patterned Sapphire Substrates. Japanese Journal of Applied Physics, 2002, 41, 2484-2488.	1.5	22
79	Free excitons in cubic CdS films. Applied Physics Letters, 2002, 80, 267-269.	3.3	20
80	Luminescence properties of lithium-doped ZnS epitaxial layers grown by MOCVD. Journal of Crystal Growth, 2002, 237-239, 1570-1574.	1.5	5
81	Structural Characterization of High-Quality ZnS Epitaxial Layers Grown on GaAs Substrates by Low-Pressure Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2001, 40, 6993-6997.	1.5	7
82	Temperature dependence of electric-field induced photoluminescence from an InGaN-based light-emitting diode. Journal of Applied Physics, 2001, 89, 5779-5781.	2.5	3
83	Photoluminescence characterization of MBE-grown ZnTexSe1â^'x epitaxial layers with high Te concentrations. Journal of Crystal Growth, 2000, 214-215, 220-224.	1.5	8
84	Magneto-luminescence spectroscopy of biexcitons in ZnS epitaxial layers. Journal of Crystal Growth, 2000, 214-215, 815-818.	1.5	1
85	Room-temperature 340nm ultraviolet electroluminescence from ZnS-based light-emitting diodes. Journal of Crystal Growth, 2000, 214-215, 1091-1095.	1.5	17
86	Optical and structural properties of high-quality ZnS epitaxial layers grown on GaAs substrates by low-pressure metalorganic chemical vapor deposition. Journal of Crystal Growth, 2000, 221, 388-392.	1.5	4
87	Defect identification in homoepitaxial- and ELO-grown GaN layers using bound-exciton Zeeman spectroscopies. Journal of Crystal Growth, 2000, 210, 216-219.	1.5	0
88	Dense excitonic luminescence and optical gain in ZnS-based quantum wells. Journal of Luminescence, 2000, 87-89, 140-144.	3.1	9
89	Ultraviolet emission properties in InxGa1â^'xN epitaxial layer revealed by magnetoluminescence and time-resolved luminescence studies. Journal of Luminescence, 2000, 87-89, 1199-1201.	3.1	1
90	Effects of electric field on photoluminescence spectra in InGaN ultraviolet light-emitting diodes. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 7, 949-952.	2.7	3

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91	Growth of Bulk GaN Single Crystals by the Pressure-Controlled Solution Growth Method. Japanese Journal of Applied Physics, 2000, 39, 2394-2398.	1.5	16
92	Radiative recombination mechanisms in InGaN/AlGaN single-quantum-well LED revealed by time-resolved photoluminescence spectra under external electric fields. , 2000, , .		0
93	Recombination dynamics of carriers in an InGaN/AlGaN single-quantum-well light-emitting diode under reverse-bias voltages. Applied Physics Letters, 2000, 76, 1546-1548.	3.3	12
94	Optical properties of biexcitons in ZnS. Physical Review B, 2000, 61, 8363-8368.	3.2	34
95	Dependence of Exciton -- Longitudinal-Optical-Phonon Interaction Energy on Well Width in Cd0.2Zn0.8Se/ZnSe Multiple-Quantum Wells. Japanese Journal of Applied Physics, 1999, 38, L808-L810.	1.5	3
96	Excitonic Emissions under High Excitation of Hexagonal GaN Single Crystal Grown by Sublimation Method. Japanese Journal of Applied Physics, 1999, 38, L102-L104.	1.5	11
97	Reduction of Inhomogeneous Broadening of Exciton Luminescence in CdxZn1-xSe Ternary Alloys and CdxZn1-xSeâ€“ZnSe Multiple Quantum Wells Grown by Molecular-Beam Epitaxy under Se-Excess Supply. Japanese Journal of Applied Physics, 1999, 38, 3550-3555.	1.5	3
98	Time-resolved spectroscopy of excitonic luminescence from GaN homoepitaxial layers. Journal of Applied Physics, 1999, 86, 7186-7188.	2.5	13
99	Localized biexcitons and optical gain in ZnS-based quantum wells. Electronics and Communications in Japan, 1999, 82, 64-72.	0.2	0
100	Recombination Dynamics of Self-Trapped Excitons in the High-Efficient Blue LEDs under Reverse Bias Condition. , 1999, , .		2
101	Improvement of high laser-resistance surface in CLBO by ion beam etching. The Review of Laser Engineering, 1999, 27, 123-125,128.	0.0	0
102	Structural properties and intense ultraviolet emission of polycrystalline GaN films on AlN ceramics grown by N plasma-excited CVD. Journal of Crystal Growth, 1998, 189-190, 223-226.	1.5	2
103	Blue radiative recombination due to hot electrons in InGaN single-quantum well LEDs. Journal of Crystal Growth, 1998, 189-190, 812-815.	1.5	3
104	Temperature dependence of excitonic luminescence from high-quality ZnS epitaxial layers. Journal of Crystal Growth, 1998, 184-185, 1110-1113.	1.5	25
105	Effects of Si-doping on luminescence properties of InxGa1â^'xN epitaxial layers. Journal of Crystal Growth, 1998, 189-190, 611-615.	1.5	8
106	Effect of High Current Injection on the Blue Radiative Recombination in InGaN Single Quantum Well Light Emitting Diodes. Japanese Journal of Applied Physics, 1998, 37, 1462-1464.	1.5	1
107	Ultraviolet stimulated emission due to biexciton decay process in ZnS-based quantum wells. Applied Physics Letters, 1997, 70, 1429-1431.	3.3	17
108	Blue Semiconductor Lasers. Lasing Mechanism of Blue and Ultraviolet Semiconductor Lasers.. The Review of Laser Engineering, 1997, 25, 493-497.	0.0	0

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109	Effects of high excitation on localized excitons in cubic ZnCdS lattice matched to GaAs. Journal of Crystal Growth, 1996, 159, 830-834.	1.5	0
110	Dynamics of dense excitonic systems in ZnSe-based single quantum wells. Journal of Crystal Growth, 1996, 159, 814-817.	1.5	0
111	Effect of external uniaxial stress on the green-blue emission of a CdZnSe strained quantum well under high excitation. Journal of Crystal Growth, 1996, 159, 676-679.	1.5	1
112	Biexciton luminescence from cubic ZnS epitaxial layers. Applied Physics Letters, 1996, 69, 88-90.	3.3	39
113	Recombination dynamics of localized excitons in a CdSe/ZnSe/ZnSxSe1â^'xsingle-quantum-well structure. Physical Review B, 1996, 54, 2629-2634.	3.2	46
114	Biexciton Luminescence from GaN Epitaxial Layers. Japanese Journal of Applied Physics, 1996, 35, L787-L789.	1.5	38
115	Excitonic Emission in GaN Films on AlN Substrates Using Microwave-Excited N Plasma Method. Japanese Journal of Applied Physics, 1996, 35, 1424-1427.	1.5	6
116	Optically pumped CdZnSe/ZnSe blueâ€green vertical cavity surface emitting lasers. Applied Physics Letters, 1995, 66, 2929-2931.	3.3	11
117	Time-resolved spectroscopy of biexciton luminescence inZnxCd1â^'xSe-ZnSySe1â^'ymultiple quantum wells. Physical Review B, 1995, 51, 2596-2599.	3.2	26
118	Time-resolved nonlinear luminescence of biexcitons in ZnSe-ZnxMg1â^'xSySe1â^'ysingle quantum wells. Physical Review B, 1995, 52, R2289-R2292.	3.2	32
119	Time-resolved spectroscopy of biexciton luminescence in wide-bandgap II-VI quantum wells. Superlattices and Microstructures, 1994, 15, 33.	3.1	14
120	Ultraviolet lasing and excitonic gain in CdxZn1â^'xS-ZnS strained-layer multiple quantum wells. Journal of Crystal Growth, 1994, 138, 570-574.	1.5	6
121	Localized excitons in cubicZn1â^'xCdxS lattice matched to GaAs. Physical Review B, 1994, 50, 14655-14658.	3.2	43
122	Interface properties and the effect of strain of ZnSe/ZnS strained-layer superlattices. Physica B: Condensed Matter, 1993, 191, 23-44.	2.7	36
123	Formation of optical gain due to exciton localization in CdxZn1â^'xS-ZnS strained-layer quantum wells. Physica B: Condensed Matter, 1993, 191, 83-89.	2.7	22
124	Band Offsets in CdZnS/ZnS Strained-Layer Quantum Well and Its Application to UV Laser Diode. Japanese Journal of Applied Physics, 1993, 32, L1308-L1311.	1.5	44
125	Ultraviolet stimulated emission and optical gain spectra in CdxZn1â^'xSâ€ZnS strainedâ€layer superlattices. Applied Physics Letters, 1992, 61, 2190-2192.	3.3	76
126	Hydrostatic pressure dependence of two-dimensional exciton luminescence in ZnSe/ZnS strained-layer superlattices. Surface Science, 1992, 267, 129-132.	1.9	3

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127	Hydrostatic-pressure-induced type-I â†' type-II conversion in ZnSe-ZnS strained-layer superlattices. Journal of Crystal Growth, 1992, 117, 484-487.	1.5	4
128	New characterization method of biaxial stress by Raman scattering: demonstration in ZnSe-ZnS strained-layer superlattices. Journal of Crystal Growth, 1992, 117, 488-491.	1.5	4
129	Type conversion under hydrostatic pressure in ZnSe-ZnS strained-layer superlattices. Physical Review B, 1991, 44, 1801-1805.	3.2	35
130	Biaxial splitting of optical phonon modes in ZnSeâ€ZnS strainedâ€layer superlattices. Applied Physics Letters, 1991, 58, 2135-2137.	3.3	20
131	Epitaxial growth and photoluminescence characterization of ZnSe: Na films by low-pressure MOCVD. Journal of Crystal Growth, 1990, 99, 408-412.	1.5	7
132	Excitonic luminescence and the effect of high excitation in ZnSeî—¸ZnS strained-layer superlattices grown on ZnS substrates. Journal of Crystal Growth, 1990, 101, 661-666.	1.5	21
133	Bound-Exciton and Edge-Emission Spectra Associated with Li and Na Acceptors in ZnSe. Japanese Journal of Applied Physics, 1989, 28, L837-L840.	1.5	24
134	Excitonic Properties of ZnSe-ZnS Strained-Layer Superlattices and A Fibonacci Sequence. Materials Research Society Symposia Proceedings, 1989, 161, 199.	0.1	14
135	Effect of Strain on Bound Excitons in High-Purity ZnSe Bulk and MOCVD Homoepitaxially-Grown ZnSe Layer. Materials Research Society Symposia Proceedings, 1987, 102, 143.	0.1	2